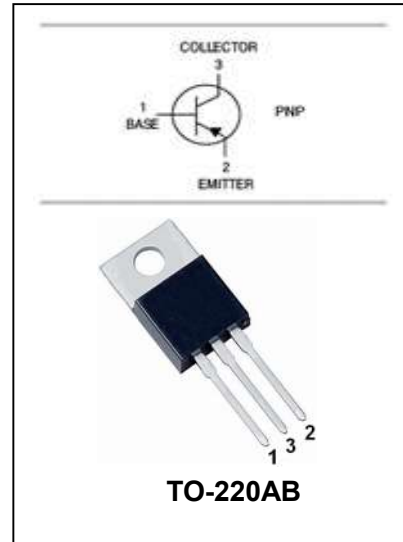


PNP Epitaxial Planar Silicon Transistors

2SB1274

FEATURES

- Good Linearity of h_{fe} .
- Complementary to KTD2060



MAXIMUM RATING operating temperature range applies unless otherwise specified

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-4	A
I_B	Base Current	-0.4	A
P_C	Collector Dissipation $T_c=25^\circ\text{C}$	25	W
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$

PNP Epitaxial Planar Silicon Transistors

2SB1274

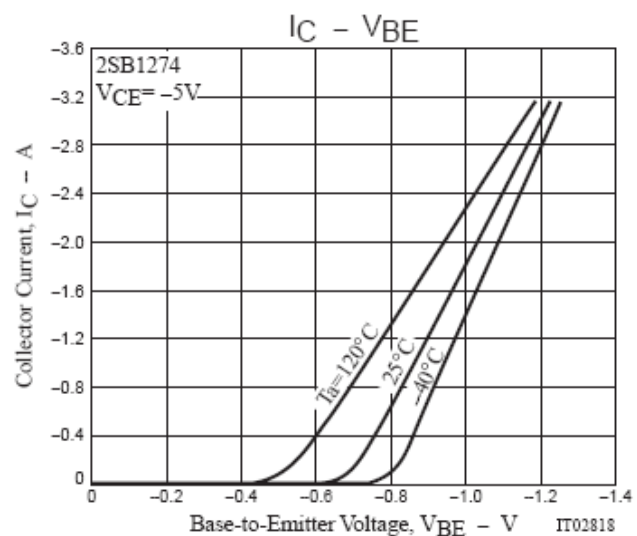
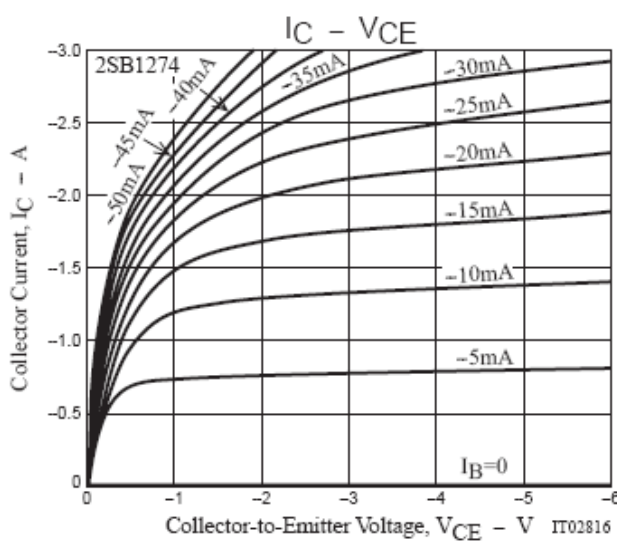
ELECTRICAL CHARACTERISTICS Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -50mA, I_B = 0$	-80			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -80V, I_E = 0$			-30	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-100	μA
DC Current Gain	h_{FE}	$V_{CE} = -5V, I_C = -0.5A$	40		240	
		$V_{CE} = -5V, I_C = -3A$	15			
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -2A, I_B = -0.2A$		-0.4	-1.0	V
Base-emitter Voltage	V_{BE}	$I_C = -0.5A, V_{CE} = -5V$		-0.8	-1.0	V
Transition Frequency	f_T	$V_{CE} = -5V, I_E = -0.5A$		100		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0,$ $f = 1MHz$		60		pF

CLASSIFICATION OF h_{FE}

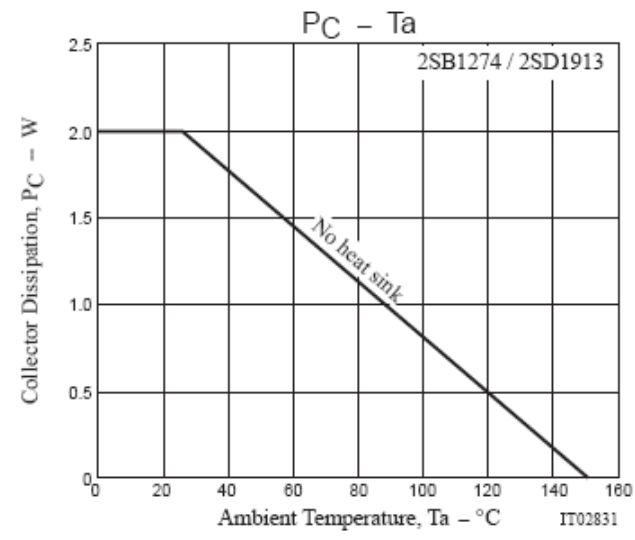
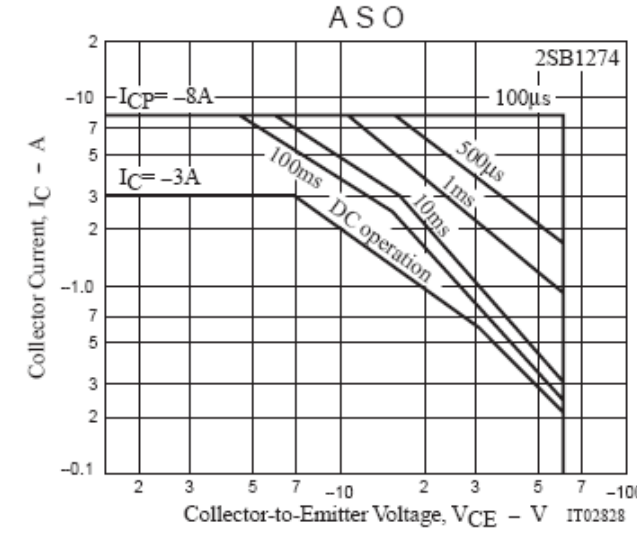
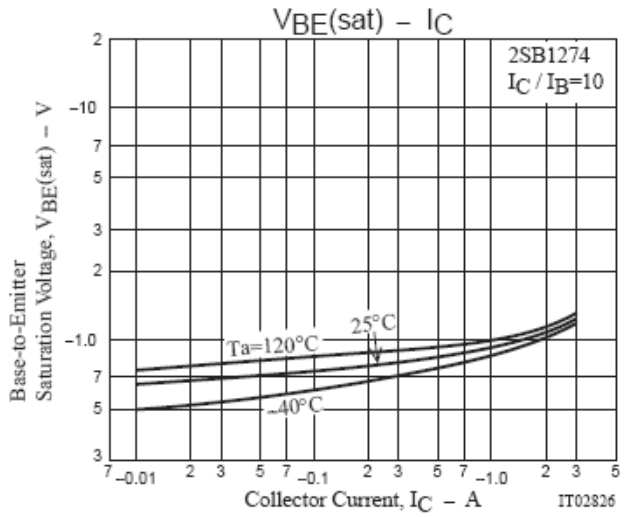
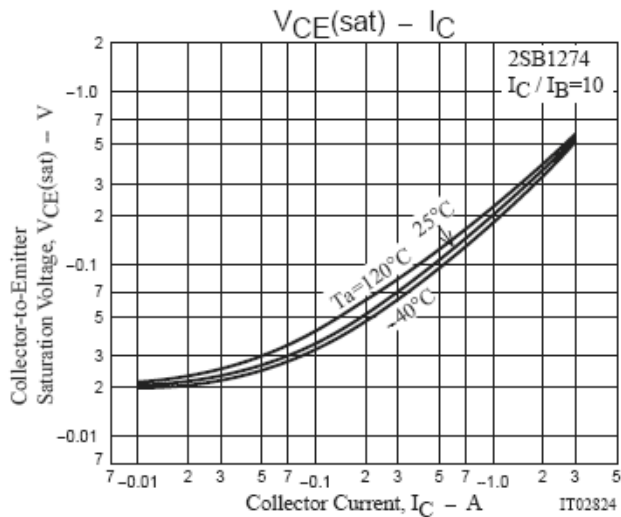
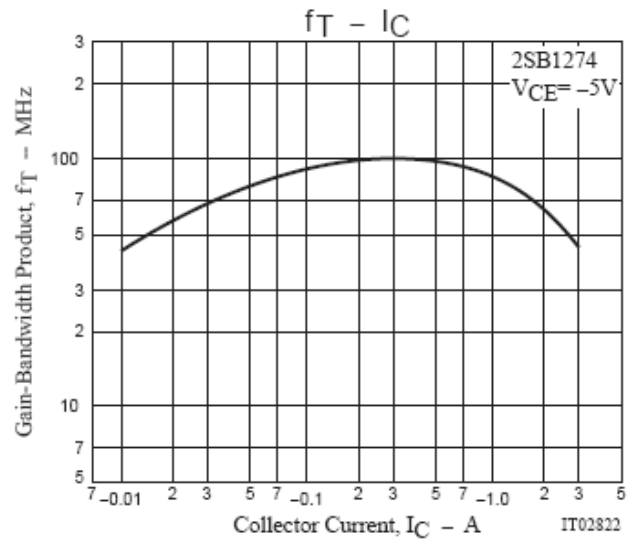
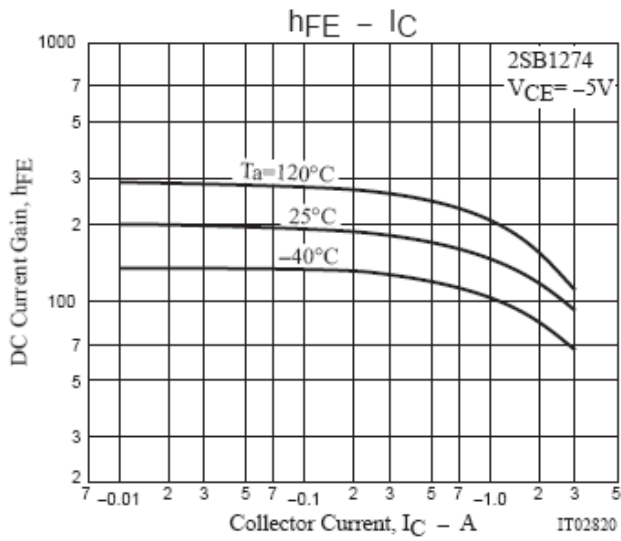
Range	Q	R	S
Marking	70-140	100-200	140-280

TYPICAL CHARACTERISTICS @ $T_a = 25^\circ C$ unless otherwise specified



PNP Epitaxial Planar Silicon Transistors

2SB1274



PNP Epitaxial Planar Silicon Transistors

2SB1274

PACKAGE OUTLINE

Plastic surface mounted package

TO-220AB

